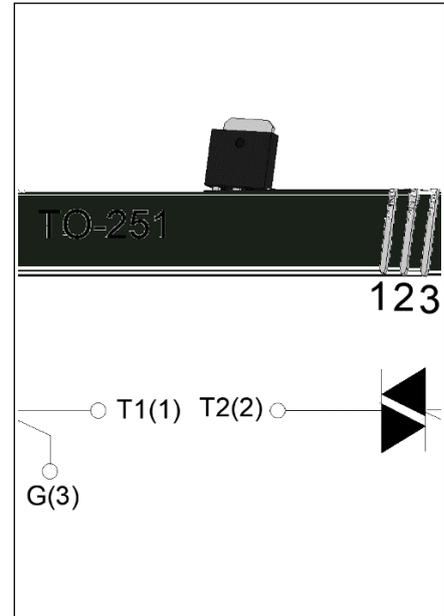




The JST134H-600E triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. From T2 terminals to external heatsink. Package TO-251 is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	4	A
$V_{DRM}/V_{RRM}$	600	V
$I_{GT} / / /$	10/10/10/25	mA

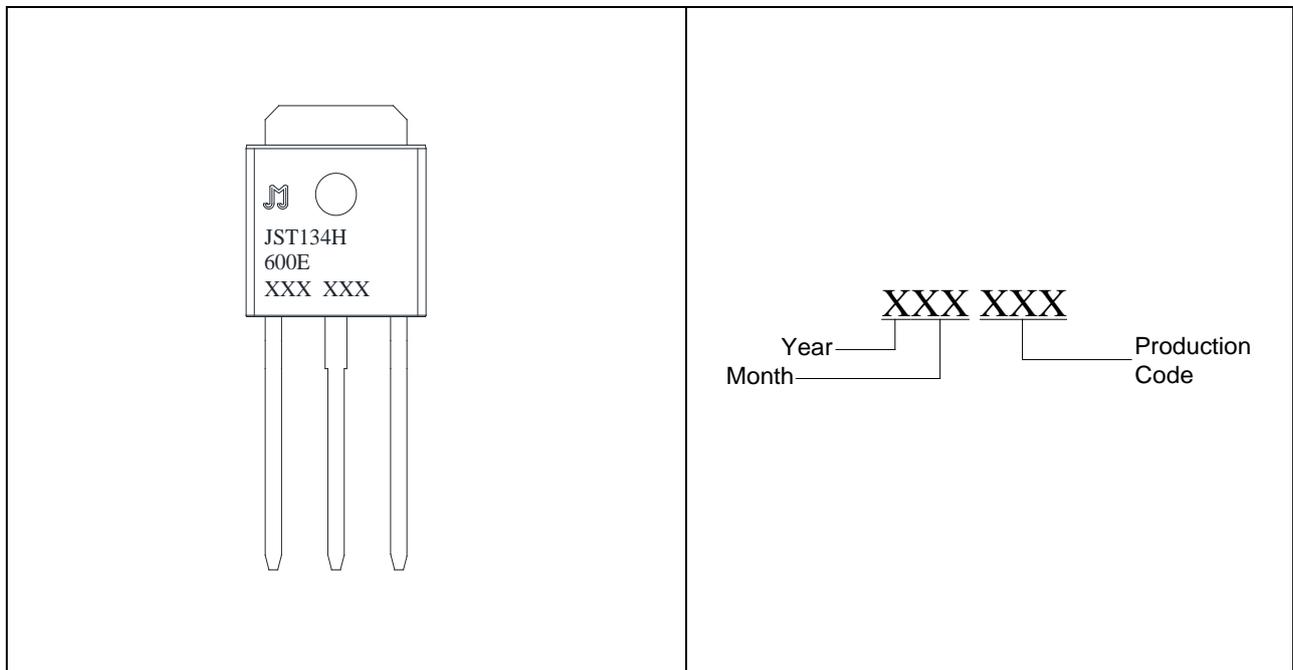
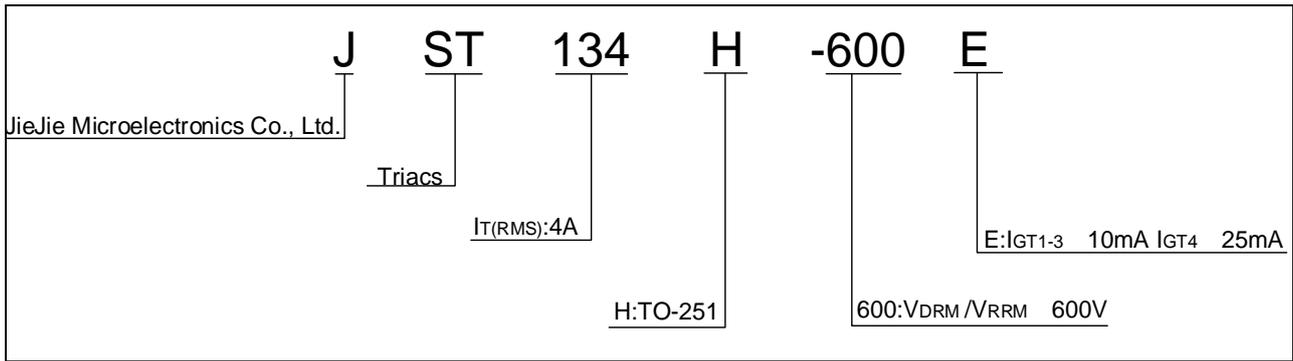
Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	
Operating junction temperature range	$T_j$	-40-125	
Repetitive peak off-state voltage ( $T_j=25^\circ C$ )	$V_{DRM}$	600	V
Repetitive peak reverse voltage ( $T_j=25^\circ C$ )	$V_{RRM}$	600	V
RMS on-state current ( $T_c = 84^\circ C$ )	$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current (full cycle, $t_p=20ms$ , $T_j=25^\circ C$ )	$I_{TSM}$	25	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6ms$ , $T_j=25^\circ C$ )		27.5	
$I^2t$ value for fusing ( $t_p=10ms$ , $T_j=25^\circ C$ )	$I^2t$	3.125	$A^2s$
Critical rate of rise of on-state current ( $I_G=2 I_{GT}$ , $f=100Hz$ , $T_j=125^\circ C$ )	$di/dt$	70	$A/\mu s$
		40	
Peak gate current ( $t_p=20\mu s$ , $T_j=125^\circ C$ )	$I_{GM}$	2	A
Average gate power dissipation ( $T_j=125^\circ C$ )	$P_{G(AV)}$	0.5	W
Peak gate power	$P_{GM}$	5	W
Peak pulse voltage ( $T_j=25^\circ C$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	4	kV

(T<sub>j</sub>=25 unless otherwise specified)

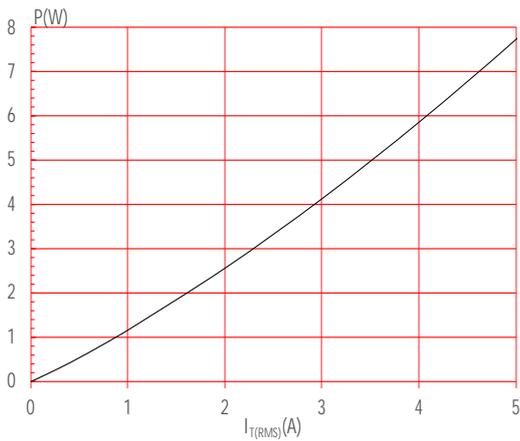
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<b>Symbol</b>	<b>Test Condition</b>	<b>Quadrant</b>	<b>Value</b>	<b>Unit</b>
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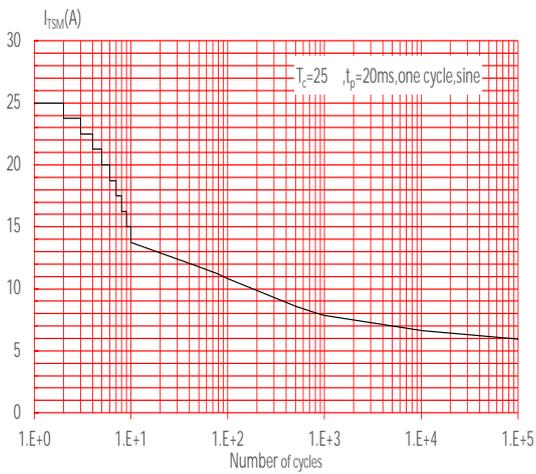
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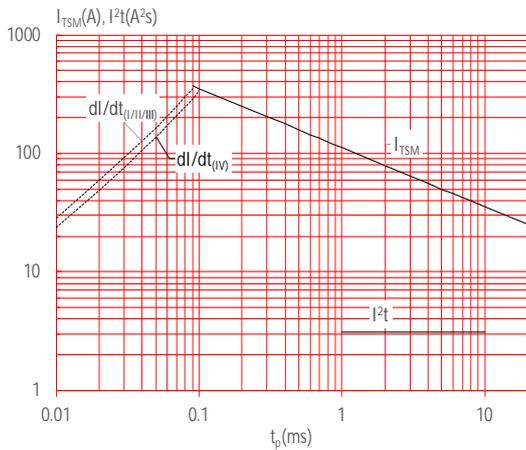
**FIG.1** Maximum power dissipation versus RMS on-state current



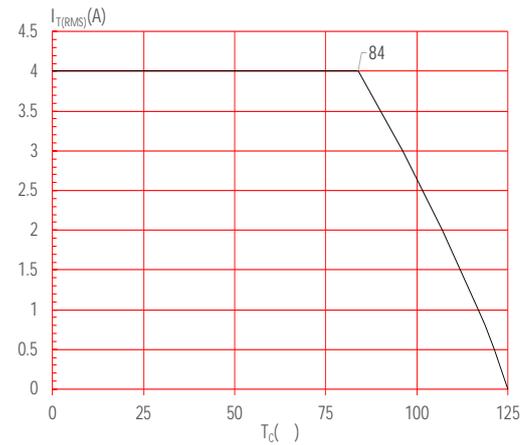
**FIG.3:** Surge peak on-state current versus number of cycles



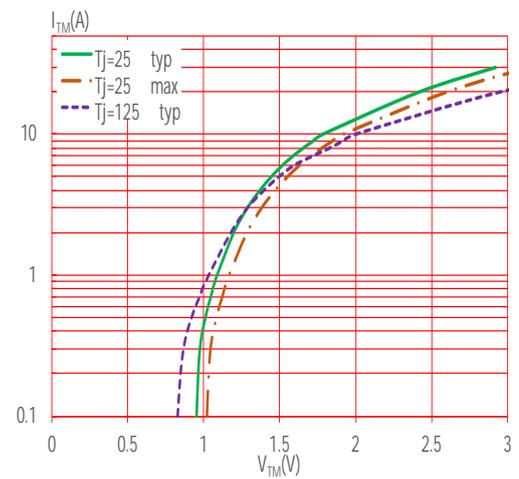
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( - - :  $di/dt < 70\text{A}/\mu\text{s}$ ; :  $di/dt < 40\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

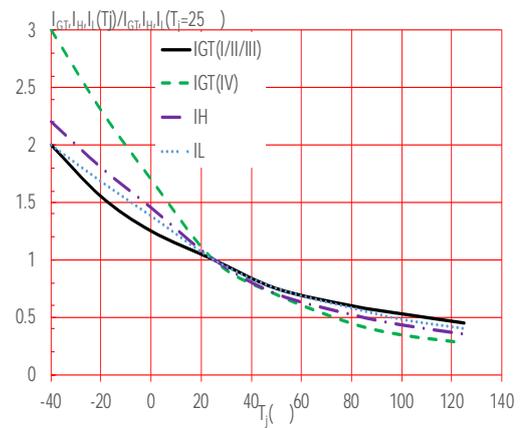
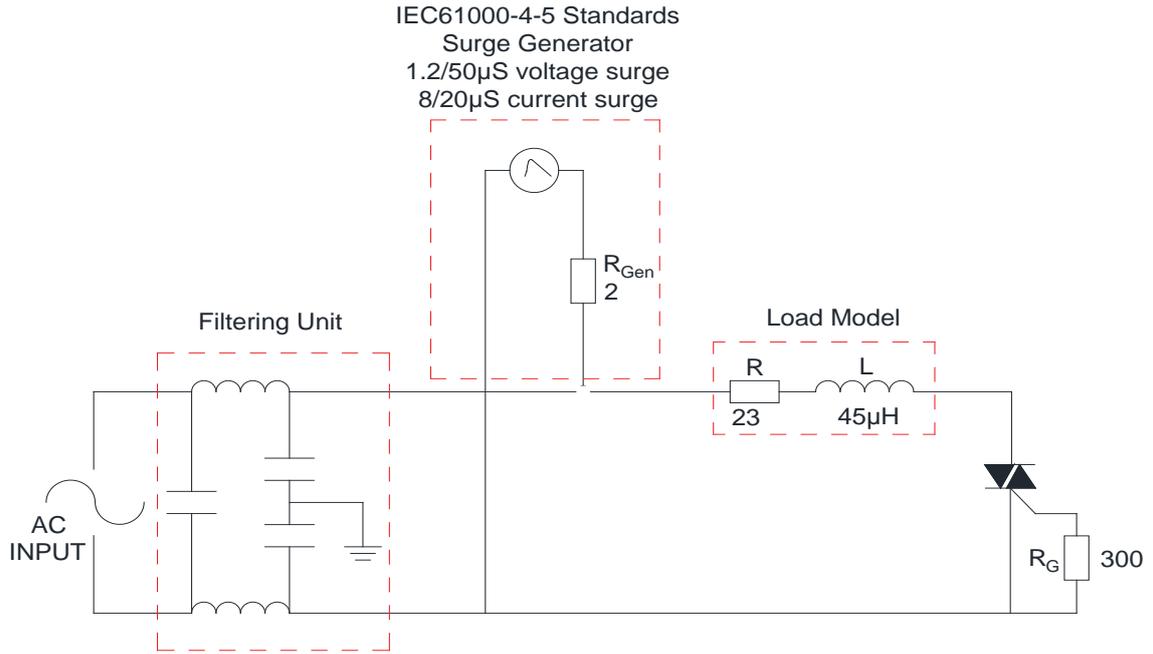


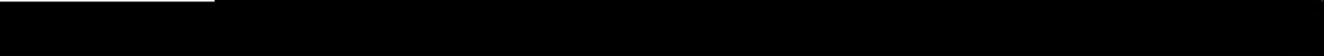
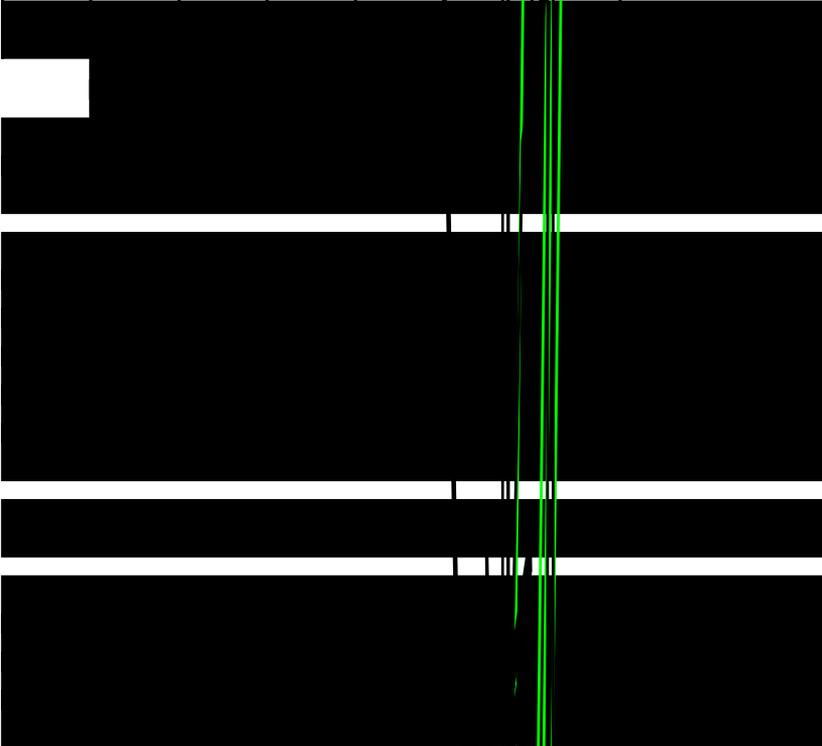
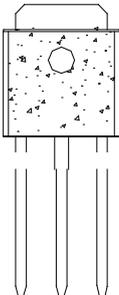
FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		H- I- J	K			
JST134H-600E	600	10	25	TO-251	80	Tube

**Document Revision History**

Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated



Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences